

### High Performance Power Factor Preregulator

### **FEATURES**

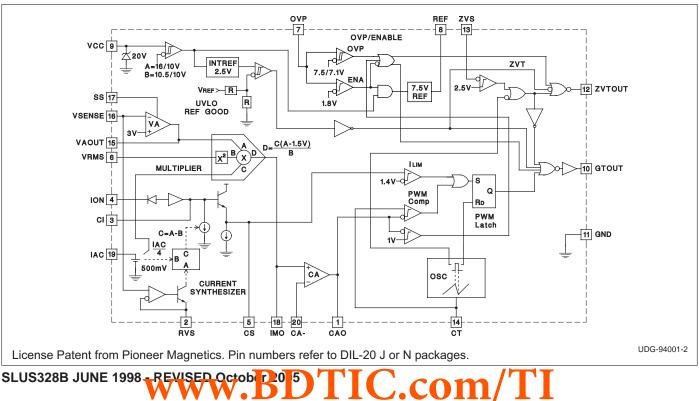
- Controls Boost PWM to Near Unity
  Power Factor
- Fixed Frequency Average Current Mode Control Minimizes Line Current Distortion
- Built-in Active Snubber (ZVT) allows Operation to 500kHz, improved EMI and Efficiency
- Inductor Current Synthesizer allows Single Current Transformer Current Sense for Improved Efficiency and Noise Margin
- Accurate Analog Multiplier with Line Compensator allows for Universal Input Voltage Operation
- High Bandwidth (5MHz), Low Offset Current Amplifier
- Overvoltage and Overcurrent protection
- Two UVLO Threshold Options
- 150µA Startup Supply Current Typical
- Precision 1% 7.5V Reference

### DESCRIPTION

The UC3855A/B provides all the control features necessary for high power, high frequency PFC boost converters. The average current mode control method allows for stable, low distortion AC line current programming without the need for slope compensation. In addition, the UC3855 utilizes an active snubbing or ZVT (Zero Voltage Transition technique) to dramatically reduce diode recovery and MOSFET turn-on losses, resulting in lower EMI emissions and higher efficiency. Boost converter switching frequencies up to 500kHz are now realizable, requiring only an additional small MOSFET, diode, and inductor to resonantly soft switch the boost diode and switch. Average current sensing can be employed using a simple resistive shunt or a current sense transformer. Using the current sense transformer method, the internal current synthesizer circuit buffers the inductor current during the switch on-time, and reconstructs the inductor current during the switch off-time. Improved signal to noise ratio and negligible current sensing losses make this an attractive solution for higher power applications.

The UC3855A/B also features a single quadrant multiplier, squarer, and divider circuit which provides the programming signal for the current loop. The internal multiplier current limit reduces output power during low line conditions. An overvoltage protection circuit disables both controller outputs in the event of a boost output OV condition.

Low startup supply current, UVLO with hysteresis, a 1% 7.5V reference, voltage amplifier with softstart, input supply voltage clamp, enable comparator, and overcurrent comparator complete the list of features. Available packages include: 20 pin N, DW, Q, J, and L.

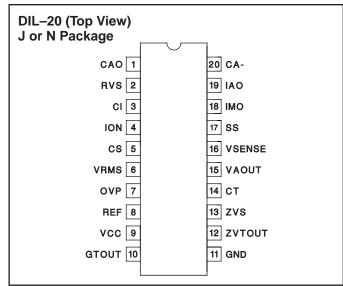


### BLOCK DIAGRAM

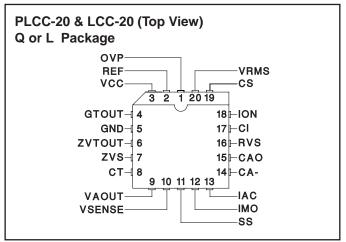
### **ABSOLUTE MAXIMUM RATINGS**

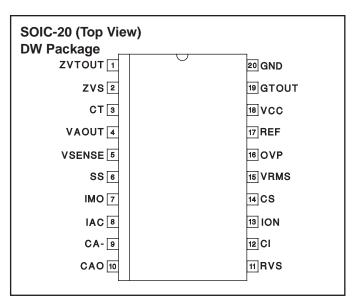
Supply Voltage VCC.      Internally Limited        VCC Supply Clamp Current      20mA
PFC Gate Driver Current (continuous) ± 0.5A
PFC Gate Driver Current (peak) ± 1.5A
ZVT Drive Current (continuous)
ZVT Drive Current (peak)±0.75A
Input Current (IAC, RT, RVA) 5mA
Analog Inputs (except Peak Limit)0.3 to 10V
Peak Limit Input
Softstart Sinking Current 1.5mA
Storage Temperature65°C to +150°C
Junction Temperature
Lead Temperature (Soldering, 10 sec.)+300°C

Currents are positive into, negative out of the specified terminal. Consult Packaging Section of Databook for thermal limitations and considerations of packages. All voltages are referenced to GND.



#### **CONNECTION DIAGRAMS**





**ELECTRICAL CHARACTERISTICS:**Unless otherwise specified: VCC = 18V, RVS = 23k, CT = 470pF, CI = 150pF, VRMS = 1.5V, IAC =  $100\mu$ A, I<sub>SENSE</sub> = 0V, CAO = 4V, VAOUT= 3.5V, VSENSE = 3V. -40°C to 85°C (UC2855A/B), 0°C to 70°C (UC3855A/B).

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Overall					
Supply Current, OFF	CAO, VAOUT = 0V, VCC = UVLO -0.3V		150	500	μA
Supply Current, OPERATING			17	25	mA
VCC Turn-On Threshold	UC3855A		15.5	17.5	V
VCCTurn-Off Threshold	UC3855A,B	9	10		V
VCC Turn-On Threshold	UC3855B		10.5	10.8	V
VCC Clamp	$I(VCC) = I_{CC(on)} + 5mA$	18	20	22	V
Voltage Amplifier					
Input Voltage		2.9		3.1	V
VSENSE Bias Current		-500	25	500	nA
Open Loop Gain	$V_{OUT} = 2 \text{ to } 5V$	65	80		dB
V <sub>OUT</sub> High	$I_{LOAD} = -300 \mu A$	5.75	6	6.25	V
Vout Low	$I_{LOAD} = 300 \mu A$		0.3	0.5	V
Output Short Circuit Current	Vout = 0V		0.6	3	mA
WWV	v.BDTIC.com/	ΊΙ			

**ELECTRICAL CHARACTERISTICS:**Unless otherwise specified: VCC = 18V, RVS = 23k, CT = 470pF, CI = 150pF, VRMS = 1.5V, IAC =  $100\mu$ A, I<sub>SENSE</sub> = 0V, CAO = 4V, VAOUT= 3.5V, VSENSE = 3V. -40°C to 85°C (UC2855A/B), 0°C to 70°C (UC3855A/B).

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNITS	
Current Amplifier		•				
Input Offset Voltage	$V_{CM} = -2.5V$	-4		4	mV	
Input Bias Current (Sense)	$V_{CM} = 2.5V$	-500		500	nA	
Open Loop Gain	$V_{CM} = 2.5V, V_{OUT} = 2 \text{ to } 6V$	80	110		dB	
Vout High	$I_{LOAD} = -500 \mu A$		6		V	
Vout Low	$I_{LOAD} = 500 \mu A$		0.3	0.5	V	
Output Short Circuit Current	$V_{OUT} = 0V$		1	3	mA	
Common Mode Range		-0.3		5	V	
Gain Bandwidth Product	F <sub>IN</sub> = 100kHz, 10mV, P–P, T <sub>A</sub> = 25°C	2.5	5		MHz	
Reference	·	•				
Output Voltage	I <sub>REF</sub> = 0mA, TA = 25°C	7.388	7.5	7.613	V	
	I <sub>REF</sub> = 0mA	7.313	7.5	7.688	V	
Load Regulation	$I_{\text{REF}} = 1 \text{ to } 10 \text{ mA}$	-15		15	mV	
Line Regulation	VCC = 15 to 35V	-10		10	mV	
Short Circuit Current	REF = 0V	20	45	65	mA	
Oscillator	·	•				
Initial Accuracy	$T_A = 25^{\circ}C$	170	200	230	kHz	
Voltage Stability	V <sub>CC</sub> = 12 to 18V		1		%	
Total Variation	Line, Temp.	160		240	kHz	
Ramp Amplitude (P–P)	Outputs at 0% duty cycle	4.7		5.7	V	
Ramp Valley Voltage		1.1		1.6	V	
Enable/OVP/Current Limit		•				
Enable Threshold			1.8	2.2	V	
OVP Threshold			7.5	7.66	V	
OVP Hysteresis		200	400	600	mV	
OVP Propagation Delay			200		ns	
OVP Input Bias Current	V= 7.5V		1	10	μA	
PKLIMIT Threshold		1.25	1.5	1.75	V	
PKLIMIT Input Current	$V_{PKLIMIT} = 1.5V$		100		μΑ	
PKLIMIT Prop. Delay			100		ns	
Soft Start						
Soft Start Charge Current		-10	-13	-20	μΑ	
Soft Start Discharge Current		2	10	20	mA	
Multiplier						
Output Current - IAC Limited	IAC = 100μA, VRMS = 1V	-235	-205	-175	μA	
Output Current - Zero	$IAC = 0\mu A$	-2	-0.2	2	μA	
Output Current - Power Limited	VRMS = 1.5V, VAOUT = 5.5V	-250	-209	-160	μA	
Output Current	VRMS = 1.5V, VAOUT = 2V		-26		μA	
	VRMS = 1.5V VAOUT = 5V		-190		μA	
	VRMS = 5V, VAOUT = 2V		-3		μA	
	VRMS = 5V, VAOUT = 5V		-17		μA	
Gain Constant	Refer to Note 1	-0.95	-0.85	-0.75	1/V	

**ELECTRICAL CHARACTERISTICS:**Unless otherwise specified: VCC = 18V, RVS = 23k, CT = 470pF, CI = 150pF, VRMS = 1.5V, IAC = 100μA, I<sub>SENSE</sub> = 0V, CAO = 4V, VAOUT= 3.5V, VSENSE = 3V. -40°C to 85°C (UC2855A/B), 0°C to 70°C (UC3855A/B).

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Gate Driver Output					
Output High Voltage	I <sub>OUT</sub> = -200mA, VCC = 15V	12	12.8		V
Output Low Voltage	$I_{OUT} = 200 \text{mA}$		1	2.2	V
Output Low Voltage	I <sub>OUT</sub> = 10mA		300	500	mV
Output Low (UVLO)	IOUT = 50mA, VCC = 0V		0.9	1.5	V
Output RISE/FALL Time	CLOAD = 1nF		35		ns
Output Peak Current	CLOAD = 10nF	0.5	1.5		A
ZVT					
ZVS Threshold		2.3	2.6	2.9	V
Input Bias Current	$V = 2.5V, V_{CT} = 0$		6	20	μA
Propagation Delay	Measured at ZVTOUT		100		ns
Maximum Pulse Width			400		ns
Output High Voltage	I <sub>OUT</sub> = -100mA, Vcc = 15V	12	12.8		V
Output Low Voltage	I <sub>OUT</sub> = 100mA		1	2.2	V
	$I_{OUT} = 10 \text{mA}$		300	900	mV
Output Low (UVLO)	$I_{OUT} = 50 \text{mA}, V_{CC} = 0 \text{V}$		0.9	1.5	V
Output RISE/FALL Time	$C_{LOAD} = 1 nF$		35		ns
Output Peak Current	$C_{LOAD} = 10 nF$	0.25	0.75		Α
Current Synthesizer					
ION to CS Offset	VION = 0V		30	50	mV
CI Discharge Current	$IAC = 50\mu A$	105	118	140	μΑ
	IAC = 500µA		5		μΑ
IAC Offset Voltage		0.3	0.65	1.1	V
ION Buffer Slew Rate			10		V/µs
ION Input Bias Current	$V_{ION} = 2V$		2	15	μΑ
RVS Output Voltage	23k from RVS to GND	2.87	3	3.13	V

Note 1: Gain constant (K) =  $\frac{IAC \bullet (VA_{OUT} - 1.5V)}{(V_{RMS}^2 \bullet IMO)}$  at V<sub>RMS</sub> = 1.5V, VA<sub>OUT</sub> = 5.5V.

#### **PIN DESCRIPTIONS**

**CA** This is the inverting input to the current amplifier. Connect the required compensation components between this pin and CAOUT. The common mode operating range for this input is between -0.3V and 5V.

**CAO:** This is the output of the wide bandwidth current amplifier and one of the inputs to the PWM duty cycle comparator. The output signal generated by this amplifier commands the PWM to force the correct input current. The output can swing from 0.1V to 7.5V.

**CI**: The level shifted current sense signal is impressed upon a capacitor connected between this pin and GND. The buffered current sense transformer signal charges the capacitor when the boost switch is on. When the switch is off, the current synthesizer discharges the capacitor at a rate proportional to the dl/dt of the boost inductor current. In this way, the discharge current is approximately equal to

$$\frac{3V}{RRVS} - \frac{IAC}{4}.$$

Discharging the CI capacitor in this fashion, a "reconstructed" version of the inductor current is generated using only one current sense transformer.

#### **PIN DESCRIPTIONS (cont.)**

**CS:** The reconstructed inductor current waveform generated on the CI pin is level shifted down a diode drop to this pin. Connect the current amplifier input resistor between CS and the inverting input of the current amplifier. The waveform on this pin is compared to the multiplier output waveform through the average current sensing current amplifier. The input to the peak current limiting comparator is also connected to this pin. A voltage level greater than 1.5 volts on this pin will trip the comparator and disable the gate driver output.

**CT:** A capacitor from CT to GND sets the PWM oscillator frequency according to the following equation:

$$f \approx \frac{1}{11200 \bullet CT}.$$

Use a high quality ceramic capacitor with low ESL and ESR for best results. A minimum CT value of 200pF insures good accuracy and less susceptibility to circuit layout parasitics. The oscillator and PWM are designed to provide practical operation to 500kHz.

**GND**: All voltages are measured with respect to this pin. All bypass and timing capacitors connected to GND should have leads as short and direct as possible.

**GTOUT:** The output of the PWM is a 1.5A peak totem pole MOSFET gate driver on GTOUT. A series resistor between GTOUT and the MOSFET gate of at least 10 ohms should be used to limit the overshoot on GTOUT. In addition, a low VF Schottky diode should be connected between GTOUT and GND to limit undershoot and possible erratic operation.

**IAC:** This is a current input to the multiplier. The current into this pin should correspond to the instantaneous value of the rectified AC input line voltage. This is accomplished by connecting a resistor directly between IAC and the rectified input line voltage. The nominal 650mV level present on IAC negates the need for any additional compensating resistors to accommodate for the zero crossings of the line. A current equal to one fourth of the IAC current forms one of the inductor current synthesizer inputs.

**IMO:** This is the output of the multiplier, and the noninverting input of the current amplifier. Since this output is a current, connect a resistor between this pin and ground equal in value to the input resistor of the current amplifier. The common mode operating range for this pin is -0.3V to 5V. **ION:** This pin is the current sensing input. It should be connected to the secondary side output of a current sensing transformer whose primary winding is in series with the boost switch. The resultant signal applied to this input is buffered and level shifted up a diode to the CI capacitor on the CI pin. The ION buffer has a source only output. Discharge of the CI cap is enabled through the current synthesizer circuitry. The current sense transformer termination resistor should be designed to obtain a 1V input signal amplitude at peak switch current.

**OVP:** This pin senses the boost output voltage through a voltage divider. The enable comparator input is TTL compatible and can be used as a remote shutdown port. A voltage level below 1.8V, disables VREF, oscillator, and the PWM circuitry via the enable comparator. Between 1.8V and VREF (7.5V) the UC is enabled. Voltage levels above 7.5V will set the PWM latch via the hysteretic OVP comparator and disable both ZVTOUT and GTOUT until the OVP level has decayed by the nominal hysteresis of 400mV. If the voltage divider is designed to initiate an OVP fault at 5% of OV, the internal hysteresis enables normal operation again when the output voltage has reached its nominal regulation level. Both the OVP and enable comparators have direct logical connections to the PWM output and exhibit typical propagation delays of 200ns.

**REF**: REF is the output of the precision reference. The output is capable of supplying 25mA to peripheral circuitry and is internally short circuit current limited. REF is disabled and low whenever VCC is below the UVLO threshold, and when OVP is below 1.8V. A REF "GOOD" comparator senses REF and disables the stage until REF has attained approximately 90% of its nominal value. Bypass REF to GND with a  $0.1\mu$ F or larger ceramic capacitor for best stability.

**RVS:** The nominal 3V signal present on the VSENSE pin is buffered and brought out to the RVS pin. A current proportional to the output voltage is generated by connecting a resistor between this pin and GND. This current forms the second input to the current synthesizer.

**SS:** Soft-start  $V_{SS}$  is discharged for  $V_{VCC}$  low conditions. When enabled, SS charges an external capacitor with a current source. This voltage is used as the voltage error signal during start-up, enabling the PWM duty cycle to increase slowly. In the event of a  $V_{VCC}$  dropout, the OVP/EN is forced below 1.8V (typ), SS quickly discharges to disable the PWM.

### **PIN DESCRIPTIONS (cont.)**

**VAO**: This is the output of the voltage amplifier. At a given input RMS voltage, the voltage on this pin will vary directly with the output load. The output swing is limited from approximately 100mV to 6V. Voltage levels below 1.5V on this pin will inhibit the multiplier output.

**VCC**: Positive supply rail for the IC. Bypass this pin to GND with a 1 $\mu$ F low ESL, ESR ceramic capacitor. This pin is internally clamped to 20V. Current into this clamp should be limited to less than 10mA. The UC3855A has a 15.5V (nominal) turn on threshold with 6 volts of hysteresis while the UC3855B turns on at 10.5V with 500mV of hysteresis.

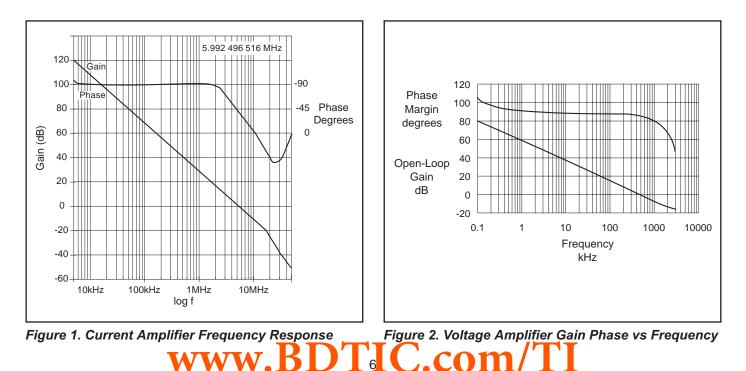
**VRMS:** This pin is the feedforward line voltage compensation input to the multiplier. A voltage on VRMS proportional to the AC input RMS voltage commands the multiplier to alter the current command signal by 1/VRMS<sup>2</sup> to maintain a constant power balance. The input to VRMS is generally derived from a two pole low pass filter/voltage divider connected to the rectified AC input voltage. This feature allows universal input supply voltage operation and faster response to input line fluctuations for the PFC boost preregulator. For most designs, a voltage level of 1.5V on this pin should correspond to low line, and 4.7V for high line. The input range for this pin extends from 0 to 5.5V.

**VSENSE**: This pin is the inverting input of the voltage amplifier and serves as the output voltage feedback point for the PFC boost converter. It senses the output voltage through a voltage divider which produces a nominal 3V. The voltage loop compensation is normally connected between this pin and VAO. The VSENSE pin must be above 1.5V at 25°C, (1.9V at -55°C) for the current synthesizer to work properly.

**ZVS:** This pin senses when the drain voltage of the main MOSFET switch has reached approximately zero volts, and resets the ZVT latch via the ZVT comparator. A minimum and maximum ZVTOUT pulse width are programmable from this pin. To directly sense the  $\approx$ 400V drain voltage of the main switch, a blocking diode is connected between ZVS and the high voltage drain. When the drain reaches 0V, the level on ZVS is  $\approx$ 0.7V which is below the 2.6V ZVT comparator threshold. The maximum ZVTOUT pulse width is approximately equal to the oscillator blanking period time.

**ZVTOUT:** The output of the ZVT block is a 750mA peak totem pole MOSFET gate driver on ZVTOUT. Since the ZVT MOSFET switch is typically 3X smaller than the main switch, less peak current is required from this output. Like GTOUT, a series gate resistor and Schottky diode to GND are recommended. This pin may also be used as a high current synchronization output driver.

For more information see Unitrode Applications Note U-153.



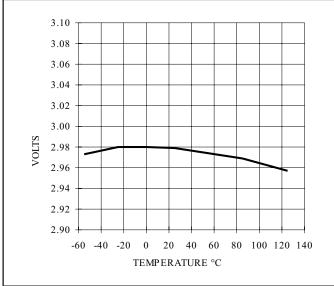


Figure 3. Voltage Amplifier Input Threshold

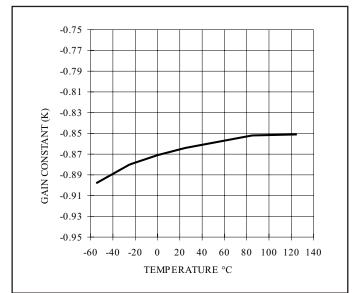


Figure 5. Multiplier Current Gain Constant

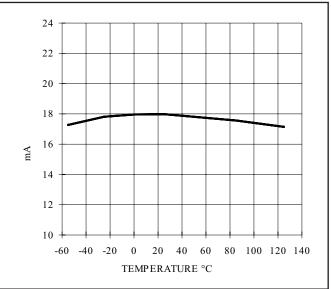


Figure 4. Supply Current ON

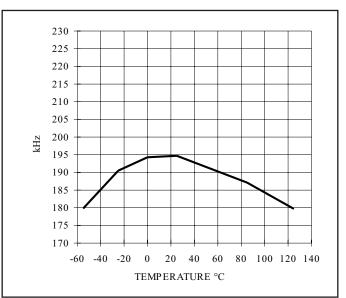


Figure 6. Oscillator Initial Accuracy

### TYPICAL APPLICATION

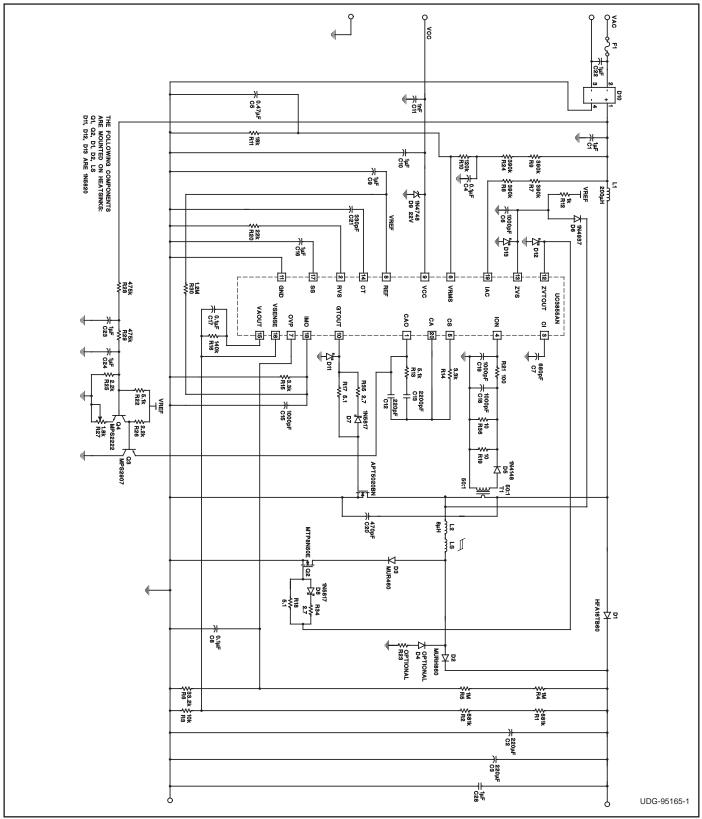


Figure 7. Typical Application

www.ti.com

27-Aug-2009

### **PACKAGING INFORMATION**

Orderable Device	Status <sup>(1)</sup>	Package Type	Package Drawing	Pins	Package Qty	e Eco Plan <sup>(2)</sup>	Lead/Ball Finish	MSL Peak Temp <sup>(3)</sup>
UC2855ADW	ACTIVE	SOIC	DW	20	25	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
UC2855ADWG4	ACTIVE	SOIC	DW	20	25	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
UC2855AN	ACTIVE	PDIP	Ν	20	20	Green (RoHS & no Sb/Br)	CU NIPDAU	N / A for Pkg Type
UC2855ANG4	ACTIVE	PDIP	N	20	20	Green (RoHS & no Sb/Br)	CU NIPDAU	N / A for Pkg Type
UC2855BDW	ACTIVE	SOIC	DW	20	25	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
UC2855BDWG4	ACTIVE	SOIC	DW	20	25	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
UC2855BDWTR	ACTIVE	SOIC	DW	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
UC2855BDWTR/81363G4	PREVIEW	SOIC	DW	20		TBD	Call TI	Call TI
UC2855BDWTRG4	ACTIVE	SOIC	DW	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
UC2855BN	ACTIVE	PDIP	Ν	20	20	Green (RoHS & no Sb/Br)	CU NIPDAU	N / A for Pkg Type
UC2855BNG4	ACTIVE	PDIP	N	20	20	Green (RoHS & no Sb/Br)	CU NIPDAU	N / A for Pkg Type
UC3855ADW	ACTIVE	SOIC	DW	20	25	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
UC3855ADWG4	ACTIVE	SOIC	DW	20	25	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
UC3855ADWTR	ACTIVE	SOIC	DW	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
UC3855ADWTRG4	ACTIVE	SOIC	DW	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
UC3855AN	ACTIVE	PDIP	Ν	20	20	Green (RoHS & no Sb/Br)	CU NIPDAU	N / A for Pkg Type
UC3855ANG4	ACTIVE	PDIP	Ν	20	20	Green (RoHS & no Sb/Br)	CU NIPDAU	N / A for Pkg Type
UC3855BDW	ACTIVE	SOIC	DW	20	25	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
UC3855BDWG4	ACTIVE	SOIC	DW	20	25	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
UC3855BDWTR	ACTIVE	SOIC	DW	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
UC3855BDWTRG4	ACTIVE	SOIC	DW	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
UC3855BN	ACTIVE	PDIP	Ν	20	20	Green (RoHS & no Sb/Br)	CU NIPDAU	N / A for Pkg Type
UC3855BNG4	ACTIVE	PDIP	Ν	20	20	Green (RoHS & no Sb/Br)	CU NIPDAU	N / A for Pkg Type

<sup>(1)</sup> The marketing status values are defined as follows: **ACTIVE:** Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in

### Addendum-Page 1 www.BDTIC.com/TI



a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available. **OBSOLETE:** TI has discontinued the production of the device.

<sup>(2)</sup> Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details. **TBD:** The Pb-Free/Green conversion plan has not been defined.

**Pb-Free (RoHS):** TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

**Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

<sup>(3)</sup> MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

**Important Information and Disclaimer:**The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

OTHER QUALIFIED VERSIONS OF UC3855A, UC3855B :

• Military: UC1855A, UC1855B

NOTE: Qualified Version Definitions:

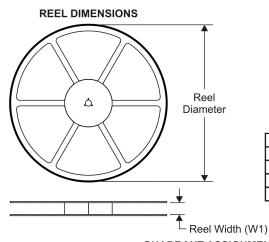
• Military - QML certified for Military and Defense Applications

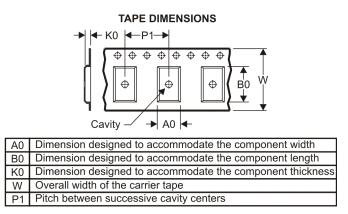
### PACKAGE MATERIALS INFORMATION

www.ti.com

Texas Instruments

### TAPE AND REEL INFORMATION





### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



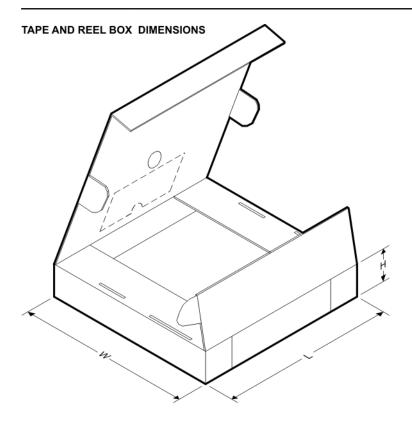
All dimensions are nominal												
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
UC2855BDWTR	SOIC	DW	20	2000	330.0	24.4	10.8	13.0	2.7	12.0	24.0	Q1
UC3855ADWTR	SOIC	DW	20	2000	330.0	24.4	10.8	13.0	2.7	12.0	24.0	Q1
UC3855BDWTR	SOIC	DW	20	2000	330.0	24.4	10.8	13.0	2.7	12.0	24.0	Q1

TEXAS INSTRUMENTS

www.ti.com

### PACKAGE MATERIALS INFORMATION

29-Jul-2009

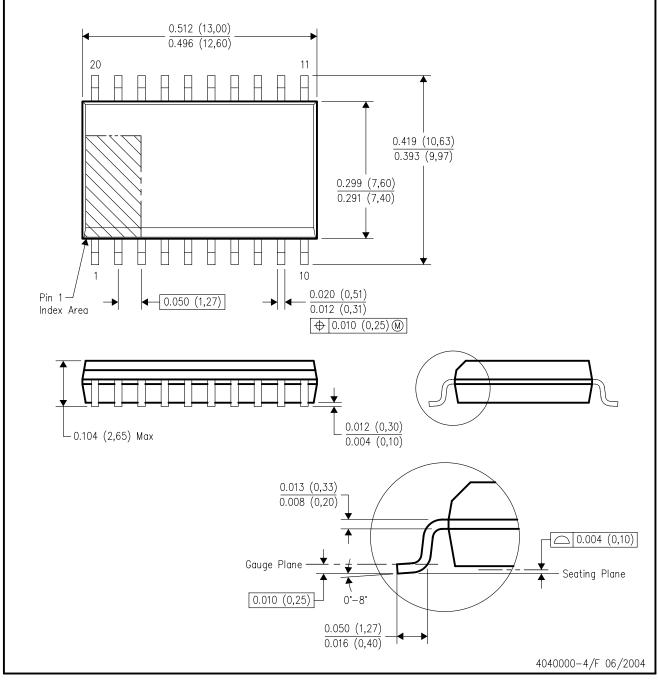


\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
UC2855BDWTR	SOIC	DW	20	2000	346.0	346.0	41.0
UC3855ADWTR	SOIC	DW	20	2000	346.0	346.0	41.0
UC3855BDWTR	SOIC	DW	20	2000	346.0	346.0	41.0

DW (R-PDSO-G20)

PLASTIC SMALL-OUTLINE PACKAGE



NOTES: A. All linear dimensions are in inches (millimeters).

B. This drawing is subject to change without notice.

C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15).

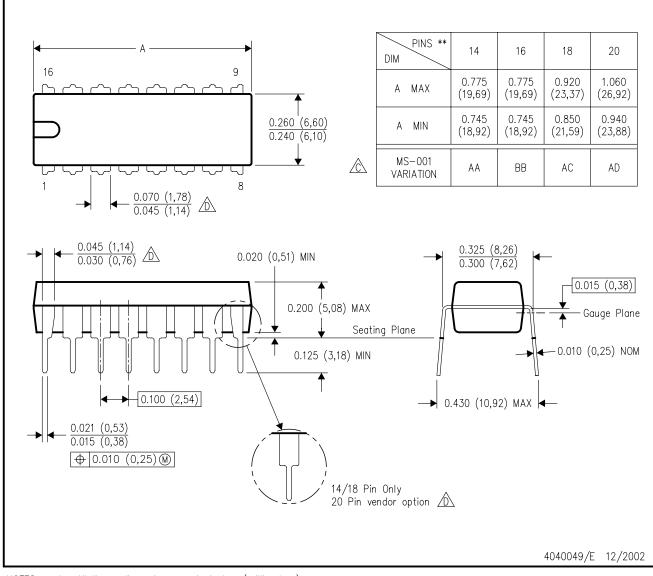
D. Falls within JEDEC MS-013 variation AC.



### N (R-PDIP-T\*\*)

PLASTIC DUAL-IN-LINE PACKAGE

16 PINS SHOWN



NOTES:

- A. All linear dimensions are in inches (millimeters).B. This drawing is subject to change without notice.
- Falls within JEDEC MS-001, except 18 and 20 pin minimum body length (Dim A).
- $\triangle$  The 20 pin end lead shoulder width is a vendor option, either half or full width.



#### **IMPORTANT NOTICE**

Texas Instruments Incorporated and its subsidiaries (TI) reserve the right to make corrections, modifications, enhancements, improvements, and other changes to its products and services at any time and to discontinue any product or service without notice. Customers should obtain the latest relevant information before placing orders and should verify that such information is current and complete. All products are sold subject to TI's terms and conditions of sale supplied at the time of order acknowledgment.

TI warrants performance of its hardware products to the specifications applicable at the time of sale in accordance with TI's standard warranty. Testing and other quality control techniques are used to the extent TI deems necessary to support this warranty. Except where mandated by government requirements, testing of all parameters of each product is not necessarily performed.

TI assumes no liability for applications assistance or customer product design. Customers are responsible for their products and applications using TI components. To minimize the risks associated with customer products and applications, customers should provide adequate design and operating safeguards.

TI does not warrant or represent that any license, either express or implied, is granted under any TI patent right, copyright, mask work right, or other TI intellectual property right relating to any combination, machine, or process in which TI products or services are used. Information published by TI regarding third-party products or services does not constitute a license from TI to use such products or services or a warranty or endorsement thereof. Use of such information may require a license from a third party under the patents or other intellectual property of the third party, or a license from TI under the patents or other intellectual property of TI.

Reproduction of TI information in TI data books or data sheets is permissible only if reproduction is without alteration and is accompanied by all associated warranties, conditions, limitations, and notices. Reproduction of this information with alteration is an unfair and deceptive business practice. TI is not responsible or liable for such altered documentation. Information of third parties may be subject to additional restrictions.

Resale of TI products or services with statements different from or beyond the parameters stated by TI for that product or service voids all express and any implied warranties for the associated TI product or service and is an unfair and deceptive business practice. TI is not responsible or liable for any such statements.

TI products are not authorized for use in safety-critical applications (such as life support) where a failure of the TI product would reasonably be expected to cause severe personal injury or death, unless officers of the parties have executed an agreement specifically governing such use. Buyers represent that they have all necessary expertise in the safety and regulatory ramifications of their applications, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of TI products in such safety-critical applications, notwithstanding any applications-related information or support that may be provided by TI. Further, Buyers must fully indemnify TI and its representatives against any damages arising out of the use of TI products in such safety-critical applications.

TI products are neither designed nor intended for use in military/aerospace applications or environments unless the TI products are specifically designated by TI as military-grade or "enhanced plastic." Only products designated by TI as military-grade meet military specifications. Buyers acknowledge and agree that any such use of TI products which TI has not designated as military-grade is solely at the Buyer's risk, and that they are solely responsible for compliance with all legal and regulatory requirements in connection with such use.

TI products are neither designed nor intended for use in automotive applications or environments unless the specific TI products are designated by TI as compliant with ISO/TS 16949 requirements. Buyers acknowledge and agree that, if they use any non-designated products in automotive applications, TI will not be responsible for any failure to meet such requirements.

Following are URLs where you can obtain information on other Texas Instruments products and application solutions:

Products		Applications	
Amplifiers	amplifier.ti.com	Audio	www.ti.com/audio
Data Converters	dataconverter.ti.com	Automotive	www.ti.com/automotive
DLP® Products	www.dlp.com	Broadband	www.ti.com/broadband
DSP	dsp.ti.com	Digital Control	www.ti.com/digitalcontrol
Clocks and Timers	www.ti.com/clocks	Medical	www.ti.com/medical
Interface	interface.ti.com	Military	www.ti.com/military
Logic	logic.ti.com	Optical Networking	www.ti.com/opticalnetwork
Power Mgmt	power.ti.com	Security	www.ti.com/security
Microcontrollers	microcontroller.ti.com	Telephony	www.ti.com/telephony
RFID	www.ti-rfid.com	Video & Imaging	www.ti.com/video
RF/IF and ZigBee® Solutions	www.ti.com/lprf	Wireless	www.ti.com/wireless

Mailing Address: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265 Copyright © 2009, Texas Instruments Incorporated